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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hyun-Jin Cho, et al.

Serial No.: 10/666,220

Filed: September 19, 2003

For: Stability in Thyristor-Based Memory Device

Tran, Mai Huong C

Group Art Unit: 2818

)

For: Stability in Thyristor-Based Memory Device

SUBMISSION OF DOCUMENTS REQUESTED BY EXAMINER

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

In the Office Action dated March 28, 2005, the Examiner requested the submission of copies of three documents. Enclosed are the requested documents. Also enclosed is a copy of a previous submitted PTO-1449 listing these references. Please initial the PTO-1449 after considering the references.

The Commissioner is authorized to charge any fees in this submission to deposit account 50-2538 (docket number C002-D-2)

Date: April 16, 2005

Respectfully submitted,

Hark C. Chan (Reg. No. 35,477)

PTO/SB/08B (08-03)

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Substitute for form 1449/PTO				Complete if Known			
Jubsuit	10 10 10 11 144 3/1 1 C			Application Number	10/666,220		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Filing Date	9/19/2003		
				First Named Inventor	Cho		
				Art Unit	2818		
				Examiner Name	Tran, Mai Huong C		
Sheet	2	of	2	Attorney Docket Number	C002-D-2		

		NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Nemati, Farid and Plummer, James, D., A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 6/1998	
		Nemati, Farid and Plummer, James, D., A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-scale Memories, International Electron Device Meeting Technical Digest, 1999	
		Gribnikov, Z.S., Korobov, V.A., and Mitin, V.V., The Tunnel Didoe as a Thyristor Emitter, Solid-State Electronics, Vol. 42, No. 9, 1998, pp. 1761-1763	
-			

Examiner	Date	
Signature	Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO:

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